Ultra-Low Resistance Dual SPDT Analog Switch

The NLAS4685 is an advanced CMOS analog switch fabricated in Sub-micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low R_{ON} of 0.8 Ω , for the Normally Closed (NC) switch and for the Normally Opened switch (NO) at 2.7 V.

The part also features guaranteed Break Before Make switching, assuring the switches never short the driver.

The NLAS4685 is available in a 2.0 x 1.5 mm bumped die array, with a 3 x 4 arrangement of solder bumps. The pitch of the solder bumps is 0.5 mm for easy handling.

Features

- Ultra–Low R_{ON} , < 0.8 Ω at 2.7 V
- Threshold Adjusted to Function with 1.8 V Control at $V_{CC} = 2.7-3.3 \text{ V}$
- Single Supply Operation from 1.8–5.5 V
- Tiny 2 x 1.5 mm Bumped Die
- Low Crosstalk, < 81 dB at 100 kHz
- Full 0–V_{CC} Signal Handling Capability
- High Isolation, -65 dB at 100 kHz
- Low Standby Current, < 50 nA
- Low Distortion, <0.14% THD
- R_{ON} Flatness of 0.15 Ω
- Pin for Pin Replacement for MAX4685
- Pb–Free Package is Available

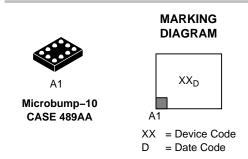
Applications

- Cell Phone
- Speaker Switching
- Power Switching (Up to 100 mA)
- Modems
- Automotive

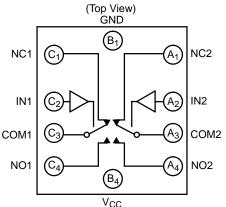


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PIN CONNECTIONS AND LOGIC DIAGRAM



FUNCTION TABLE

IN 1, 2	NO 1, 2	NC 1, 2		
0	OFF	ON OFF		
1	ON			

ORDERING INFORMATION

Device	Device Package		
NLAS4685FCT1	Microbump	3000 Tape/Reel	
NLAS4685FCT1G	Microbump (Pb–Free)	3000 Tape/Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
VIS	Analog Input Voltage (V_{NO} , V_{NC} , or V_{COM}) (Note 1)	$-0.5 \leq V_{\text{IS}} \leq V_{\text{CC}} + 0.5$	V
V _{IN}	Digital Select Input Voltage	$-0.5\leqV_{I}\leq+7.0$	V
I _{IK}	DC Current, Into or Out of Any Pin	±50	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.Signal voltage on NC, NO, and COM exceeding VCC or GND are clamped by the internal diodes. Limit forward diode current to maximum

current rating.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	1.8	5.5	V	
V _{IN}	Digital Select Input Voltage	GND	5.5	V	
V _{IS}	Analog Input Voltage (NC, NO, COM)	GND	V _{CC}	V	
T _A	Operating Temperature Range		- 55	+ 125	°C
t _r , t _f	Input Rise or Fall Time, SELECT V V	$_{\rm CC} = 3.3 \ V \pm 0.3 \ V _{\rm CC} = 5.0 \ V \pm 0.5 \ V$	0 0	100 20	ns/V

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Condition	$V_{CC} \pm 10\%$	-55°C to 25°C	<85°C	<125°C	Unit
VIH	Minimum High–Level Input		2.0	1.4	1.4	1.4	V
	Voltage, Select Inputs		2.5	1.4	1.4	1.4	
			3.0	1.4	1.4	1.4	
			5.0	2.0	2.0	2.0	
V _{IL}	Maximum Low-Level Input		2.0	0.5	0.5	0.5	V
	Voltage, Select Inputs		2.5	0.5	0.5	0.5	
			3.0	0.5	0.5	0.5	
			5.0	0.8	0.8	0.8	
I _{IN}	Maximum Input Leakage Current, Select Inputs	$V_{IN} = 5.5 V \text{ or GND}$	5.5	± 1.0	± 1.0	± 1.0	μΑ
I _{OFF}	Power Off Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	0	±10	±10	±10	μA
I _{CC}	Maximum Quiescent Supply Current	Select and $V_{IS} = V_{CC}$ or GND	5.5	± 180	± 200	± 200	nA

				Guaranteed Maximum Limit						
				–55°C	to 25°C	<8	5°C	<12	25°C	
Symbol	Parameter	Condition	$V_{CC} \pm 10\%$	Min	Max	Min	Max	Min	Max	Unit
R _{ON} (NC, NO)	"ON" Resistance (Note 2)	$V_{IN} \ge V_{IH}$ $V_{IS} = GND \text{ to } V_{CC}$ $I_{IN}I \le 100 \text{ mA}$	2.5 3.0 5.0		2.0 0.8 0.8		2.0 0.8 0.8		2.0 1.0 0.9	Ω
R _{FLAT} (NC, NO)	On–Resistance Flatness (Notes 2, 4)	$I_{COM} = 100 \text{ mA}$ $V_{IS} = 0 \text{ to } V_{CC}$	2.5 3.0 5.0		0.35 0.35 0.35		0.35 0.35 0.35		0.35 0.35 0.35	Ω
ΔR _{ON}	On–Resistance Match Between Channels (Notes 2 and 3)	$V_{IS} = 1.3 V; \\ I_{COM} = 100 \text{ mA} \\ V_{IS} = 1.5 V; \\ I_{COM} = 100 \text{ mA} \\ V_{IS} = 2.8 V; \\ I_{COM} = 100 \text{ mA} \end{cases}$	2.5 3.0 5.0		0.18 0.06 0.06		0.18 0.06 0.06		0.18 0.06 0.06	Ω
I _{NC(OFF)} I _{NO(OFF)}	NC or NO Off Leakage Current (Figure 10)	$ \begin{array}{l} V_{IN} = V_{IL} \text{ or } V_{IH} \\ V_{NO} \text{ or } V_{NC} = 1.0 \\ V_{COM} = 4.5 \ V \end{array} $	5.5	-1	1	-10	10	-150	150	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 10)	$\begin{split} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{NO} \ 1.0 \ V \text{ or } 4.5 \ V \text{ with} \\ V_{NC} \ floating \ or \\ V_{NC} \ 1.0 \ V \ or \ 4.5 \ V \text{ with} \\ V_{NO} \ floating \\ V_{COM} &= 1.0 \ V \text{ or } 4.5 \ V \end{split}$	5.5	-1	1	-10	10	-150	150	nA

DC ELECTRICAL CHARACTERISTICS – Analog Section

 Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
 ΔR_{ON =} R_{ON(MAX)} - R_{ON(MIN)} between all switches.
 Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

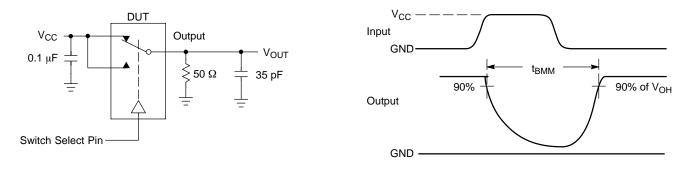
								Guaranteed Maximum Limit						
					v _{cc}	v _{is}	-55°C to 25°C		<8	5°C	<12	25°C		
Symbol		Parameter	Test 0	Conditions	(V)	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
t _{ON}	Tu	rn–On Time		2, C _L = 35 pF	2.5	1.3			55		65		70	ns
			(Figures	2 and 3)	3.0	1.5			50		60		60	
					5.0	2.8			30		35		35	
t _{OFF}	Tu	rn–Off Time	R _L = 50 9	$R_{I} = 50 \Omega, C_{I} = 35 pF$		1.3			55		65		70	ns
-			(Figures	2 and 3)	3.0	1.5			50		60		60	
					5.0	2.8			25		30		30	
t _{BBM}	Mir	nimum Break-Before-Make	V _{IS} = 3.0											ns
	Tin	ne		Ω , C _L = 35 pF	3.0	1.5	2	15						
			(Figure 1)										
			Typical @ 25, V _{CC} = 5.0 V			5.0 V V _{CC} = 3.0 V								
C _{NC} Off C _{NO} Off C _{NC} On C _{NO} On	Off NO Off Capacitance, f = 1 MHz On NC On Capacitance, f = 1 MHz							ļ	208 102 547 431			pF		

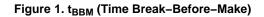
*Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted) (Note 6)

			v _{cc}	Typical	
Symbol	Parameter	Condition	V	25°C	Unit
BW	Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response	$V_{IN} = 0 \text{ dBm}$ NC/NO V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	11.5	MHz
V _{ONL}	Maximum Feed-through On Loss	V_{IN} = 0 dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	-0.05	dB
V _{ISO}	Off-Channel Isolation	f = 100 kHz; V_{IS} = 1 V RMS; C_L = 5 nF V_{IN} centered between V_{CC} and GND(Figure 4)	3.0	-65	dB
Q	Charge Injection Select Input to Common I/O	$V_{IN} = V_{CC to} \text{ GND}, R_{IS} = 0 \Omega, C_L = 1 \text{ nF}$ Q = C _L - ΔV_{OUT} (Figure 5)	3.0 5.0	15 20	рС
THD	Total Harmonic Distortion THD + Noise	$\rm F_{IS}$ = 20 Hz to 20 kHz, $\rm R_{L}$ = $\rm R_{gen}$ = 600 Ω , $\rm C_{L}$ = 50 pF $\rm V_{IS}$ = 1 V RMS	3.0	0.14	%
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; V _{IS} = 1 V RMS, C _L = 5 pF, R _L = 50 Ω V _{IN} centered between V _{CC} and GND (Figure 4)	3.0	-81	dB

5. Off–Channel Isolation = 20log10 (Vcom/Vno), Vcom = output, Vno = input to off switch. 6. -40° C specifications are guaranteed by design.





50%

t_{OFF}

90%

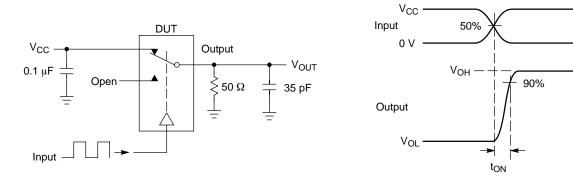
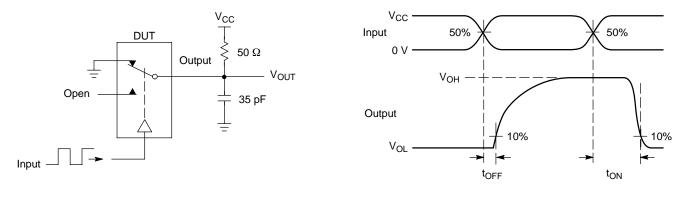
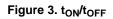
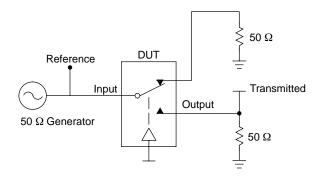


Figure 2. t_{ON}/t_{OFF}



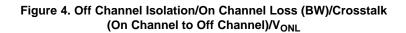




Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \ \text{ for } V_{IN} \text{ at } 100 \text{ kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \ \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL} V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω



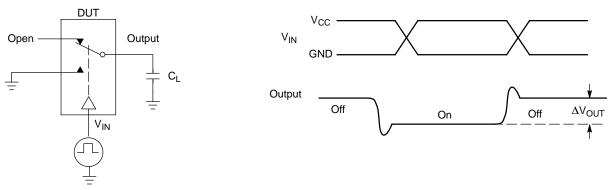


Figure 5. Charge Injection: (Q)

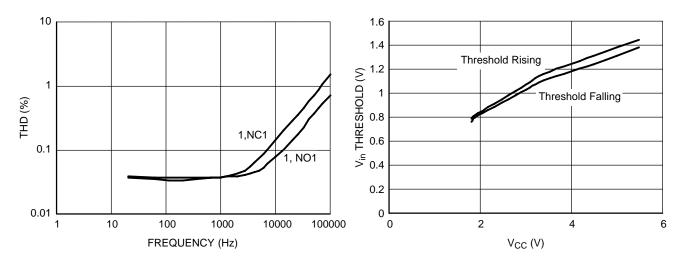




Figure 7. Voltage in Threshold on Logic Pins

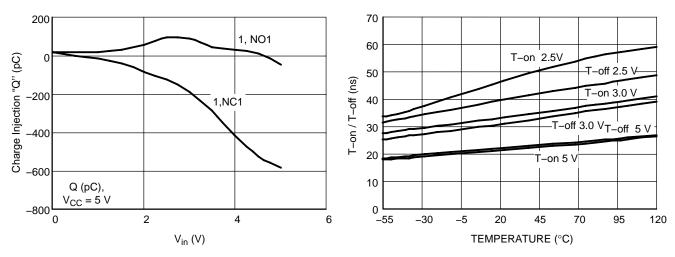
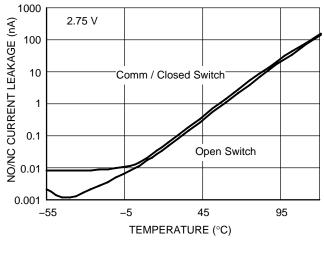
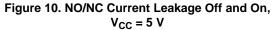
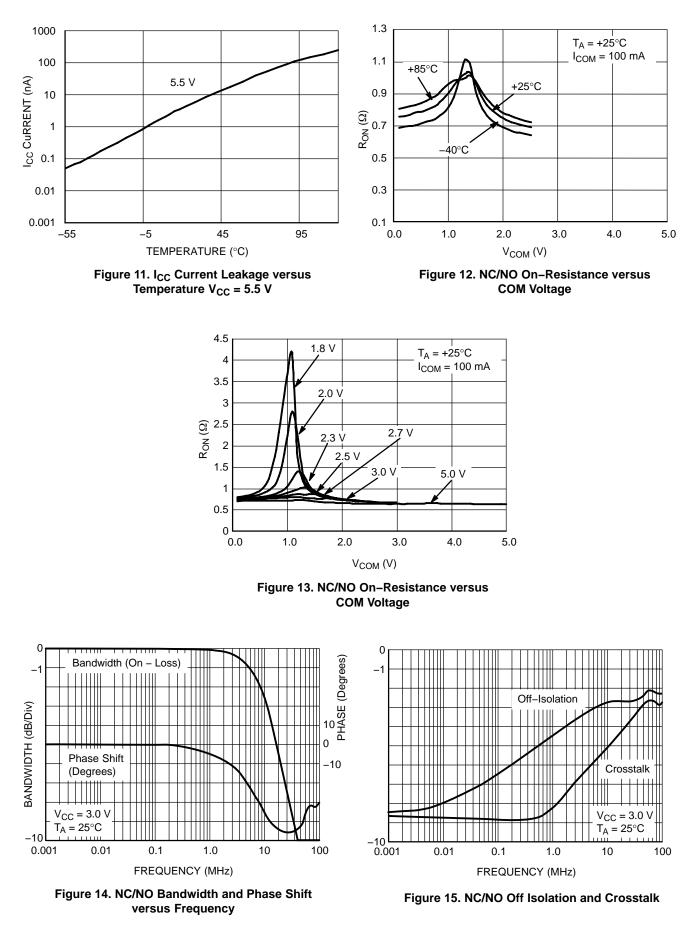


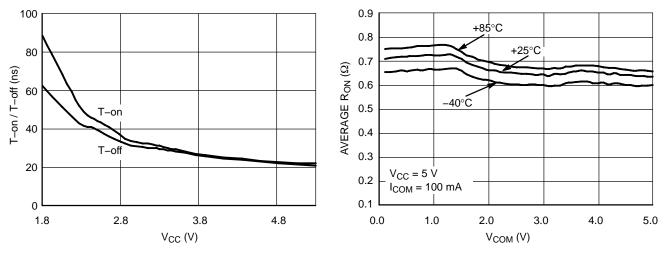
Figure 8. Charge Injection versus Vis

Figure 9. T-on/T-off Time versus Temperature









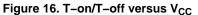


Figure 17. NC/NO On–Resistance versus COM Voltage

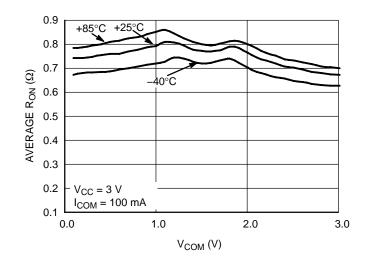


Figure 18. NC/NO On–Resistance versus COM Voltage



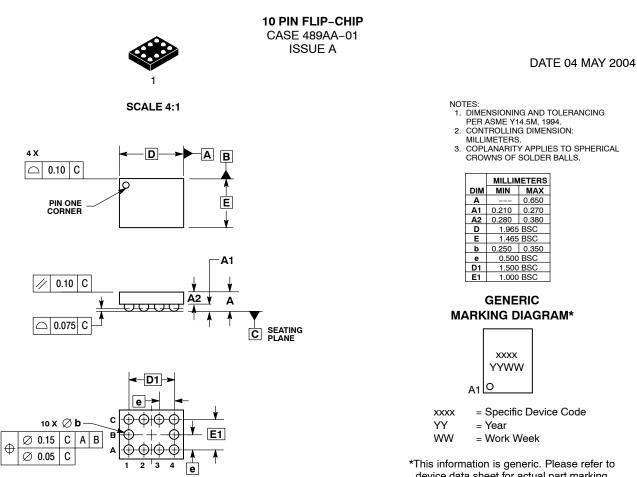


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